



PATENT
Attorney Docket No.: SAM-0274

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Min-su Kim, et al.
Serial No.: 09/994,146
Filing Date: November 26, 2001
Title: SEMICONDUCTOR DEVICE HAVING SILICON-ON-INSULATOR
STRUCTURE AND METHOD OF FABRICATING THE SAME

Examiner: Hu, S.
Group Art Unit: 2811

8/B
1.84702
9-27

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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9/16/02
Date

Lisa Sanders
Lisa Sanders

BOX NON-FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

AMENDMENT A

Sir:

This is in response to the Office Action mailed on June 17, 2002.

Please amend the application as follows:

In the Claims

- Sub D27
B1
cont.
1. (Amended) A semiconductor device having a silicon-on-insulator (SOI) structure, comprising:
 - an insulating layer;
 - an insular silicon region having first conductive impurity ions formed on the insulating layer;
 - a source region having second conductive impurity ions formed at an end of the insular silicon region;

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